Serial No. Not Yet Assigned Atty. Doc. No. 2002P17431WOUS

Amendments To The Claims:

Please amend the claims as shown. Applicants reserve the right to pursue any cancelled claims at a later date.

1.-9. (canceled)

10. (new) A process for producing single-crystal structures from metallic superalloys, comprising:

providing a substrate with a single-crystal structure from a epitaxial growth of a layer material via a first material application process;

applying an intermediate layer where no single-crystal or directional structure occurs on the substrate; and

epitaxially growing the layer material on the intermediate layer.

- 11. (new) The process as claimed in claim 10, wherein the structure is a component, a workpiece, a blade, or a vane.
- 12. (new) The process as claimed in claim 10, wherein the substrate has a plurality of single-crystal structures from the epitaxial growth of the layer material.
- 13. (new) The process as claimed in claim 10, wherein a heat treatment transforms at least part of the intermediate layer with the substrate into a region having a crystalline structure.
- 14. (new) The process as claimed in claim 10, wherein a heat treatment transforms at least part of the intermediate layer with the layer material into a region having a crystalline structure.
- 15. (new) The process as claimed in claim 10, wherein the intermediate layer is generated electrochemically.
- 16. (new) The process as claimed in claim 10, wherein the intermediate layer is applied with a non-directional microstructure.
- 17. (new) The process as claimed in claim 10, wherein the intermediate layer is applied with a directional microstructure.

Serial No. Not Yet Assigned Atty. Doc. No. 2002P17431WOUS

- 18. (new) The process as claimed in claim 10, wherein the intermediate layer is applied via a second material application process.
- 19. (new) The process as claimed in claim 10, wherein a composition ratio of constituents for the intermediate layer is adapted to a main composition ratio of main constituents of the substrate.
- 20. (new) The process as claimed in claim 10, wherein a material composition of the intermediate layer at least approximately corresponds to the material composition of the substrate.
 - 21. (new) A component formed from a metallic superalloy, comprising:
 a substrate having at least partially single-crystal structures;
 an intermediate layer having no single-crystal or directional structure in the substrate; and a layer material with a single-crystal structure is present on the intermediate layer.
- 22. (new) The component as claimed in claim 21, wherein a composition of the layer material at least approximately corresponds to a material composition of the substrate.
- 23. (new) The process as claimed in claim 21, wherein the intermediate layer is generated electrochemically.